

Abstract:

The invention relates to a method for actuating a semiconductor power switch, by which means the resistance of the switching path (E-A) of the semiconductor power switch is controlled by a control voltage (V_{st}) in such a way that the chip temperature (T_{1st} , T_{2st}) of the power switch (S_1 , S_2) does not exceed a pre-determined nominal value (T_{soll}). When the nominal temperature (T_{soll}) is reached, the resistance of the switching path (E-A) is increased. The invention also relates to a device for carrying out said method, said device using a transfer gate (TG) controlled by a charge pump (LP) as a semiconductor power switch. Commercially available transistors comprising integrated temperature sensors are used in the transfer gate (TG) as semiconductor power switches.

15

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